



Shantou Huashan Electronic Devices Co.,Ltd.

N PN SILICON TRANSISTOR

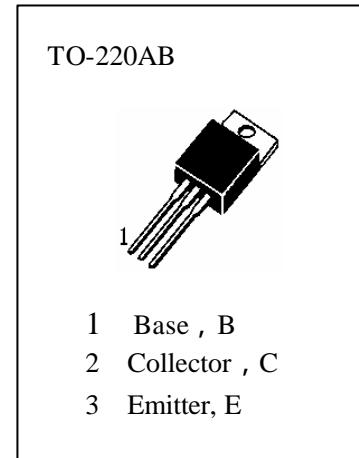
**HED880**

## APPLICATIONS

Low Frequency Power Amplifier.

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$	Storage Temperature.....	-55~150
$T_j$	Junction Temperature.....	150
$P_c$	Collector Dissipation ( $T_c=25^\circ C$ ) .....	30W
$V_{CBO}$	Collector-Base Voltage.....	60V
$V_{CEO}$	Collector-Emitter Voltage.....	60V
$V_{EBO}$	Emitter-Base Voltage.....	7V
$I_c$	Collector Current.....	3A
$I_b$	Base Current.....	0.3A



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCEO	Collector-Emitter Breakdown Voltage	60			V	$I_C=50mA, I_B=0$
ICBO	Collector Cut-off Current			100	$\mu A$	$V_{CB}=60V, I_E=0$
IEBO	Emitter Cut-off Current			100	$\mu A$	$V_{EB}=7V, I_C=0$
HFE ( 1 )	DC Current Gain	60		300		$V_{CE}=5V, I_C=0.5A$
HFE ( 2 )	DC Current Gain	20				$V_{CE}=5V, I_C=3A$
VCE(sat)	Collector- Emitter Saturation Voltage		0.4	1	V	$I_C=3A, I_B=0.3A$
VBE(on)	Base-Emitter On Voltage		0.7	1	V	$V_{CE}=5V, I_C=0.5A$
f <sub>t</sub>	Current Gain-Bandwidth Product		3		MHz	$V_{CE}=5V, I_C=0.5A,$
Cob	Output Capacitance		70		pF	$V_{CB}=10V, I_E=0, f=1MHz$
t <sub>ON</sub>	Turn-On Time		0.8		$\mu S$	$I_{B1} = -I_{B2} = 0.2A$ $V_{CC}=30V$
t <sub>STG</sub>	Storage Time		1.5		$\mu S$	
t <sub>F</sub>	Fall Time		0.8		$\mu S$	

## hFE Classification

O

Y

GR

60—120

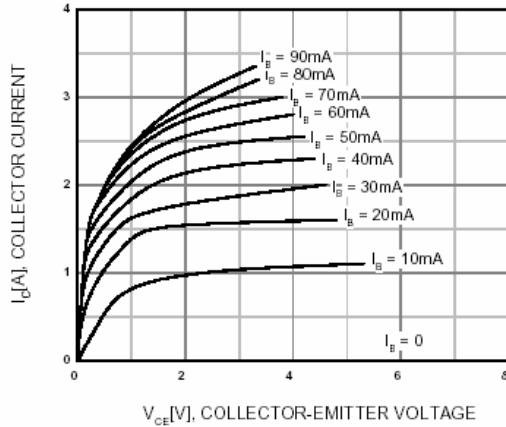
100—200

150—300

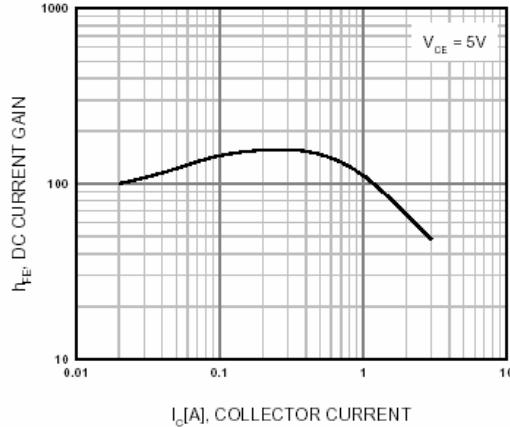


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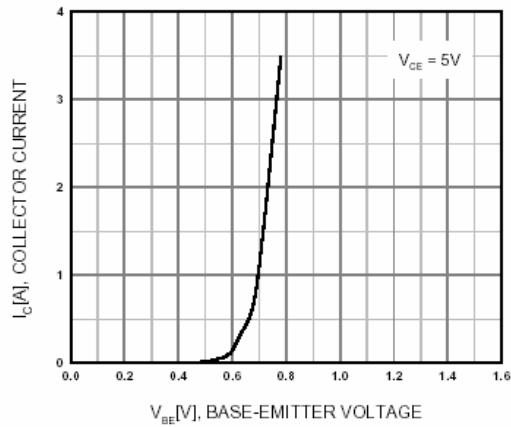
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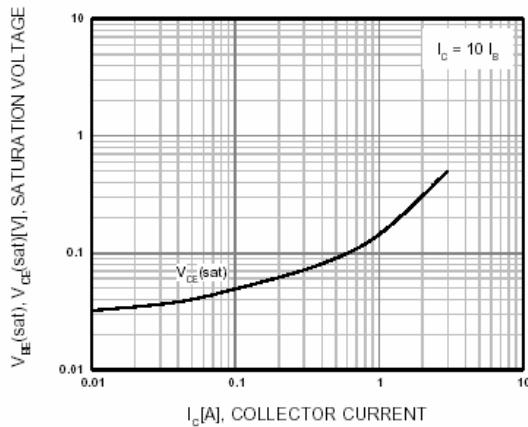
**Figure 1. Static Characteristic**



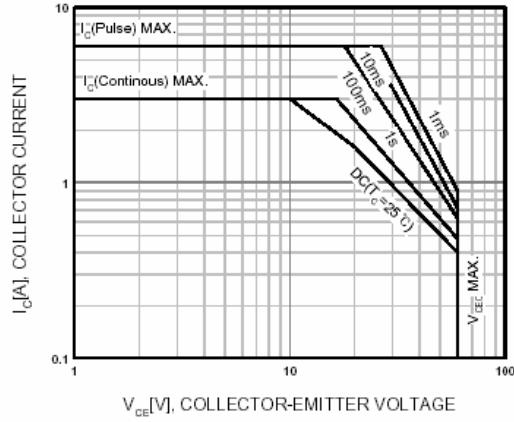
**Figure 2. DC current Gain**



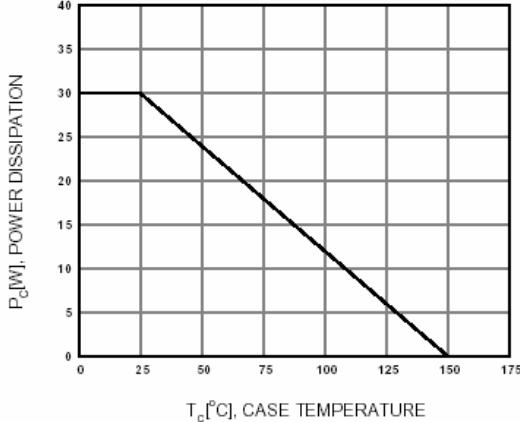
**Figure 3. Base-Emitter On Voltage**



**Figure 4. Collector-Emitter Saturation Voltage vs Collector Current**



**Figure 5. Safe Operating Area**



**Figure 6. Power Derating**